

P-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)		
- 200	119at V _{GS} = - 10 V	- 37	36 nC		

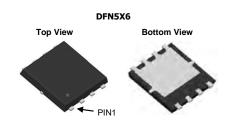
FEATURES

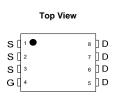
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

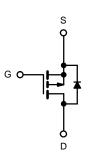


APPLICATIONS

- Active Clamp Switch
- Load Switch







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise no	oted		
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V_{DS}	- 200	V		
Gate-Source Voltage	V_{GS}	± 20	v		
	T _C = 25 °C		- 37 ^a		
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 70 °C	₋	- 20 ^a		
Continuous Diam Current (1) = 100 °C)	T _A = 25 °C	I _D	- 7.2 ^{b, c}		
	T _A = 70 °C	Ι Γ	- 5.5 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	- 105		
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 37 ^a		
Continuous Gource-Brain Blode Current	T _A = 25 °C	'S	- 7.5 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 35	7	
Single Pulse Avalanche Energy	L = 0.1 IIII I	E _{AS}	260	mJ	
	T _C = 25 °C		195		
Maximum Power Dissipation	T _C = 70 °C	P _D	124.8	w	
Maximum Tower Dissipation	T _A = 25 °C	ι υ	7.89 ^{b, c}		
	T _A = 70 °C		5.05 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature		260	7		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	16	22	°C/W		
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	0.9	1.4	C/VV		

Notes:

- a. Package limited.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 54 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 200			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 35		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1 _D = - 250 μΑ		6.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 2		- 4	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 200 V, V _{GS} = 0 V			- 1	μΑ	
	500	V _{DS} = - 200 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 37			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A}$		119	145	mΩ	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -5 \text{ V}, I_{D} = -3 \text{ A}$		23		S	
Dynamic ^b							
Input Capacitance	C _{iss}			2460		pF	
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		219			
Reverse Transfer Capacitance	C _{rss}			102			
Total Gate Charge	Q_g			36		nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = -100 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3 \text{ A}$		12			
Gate-Drain Charge	Q_{gd}			19			
Gate Resistance	R_g	f = 1 MHz		1.5		Ω	
Turn-On Delay Time	t _{d(on)}			17			
Rise Time	t _r	V_{DD} = - 100 V, R_L = 15 Ω		8		ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 3 A, V_{GEN} = - 10 V, R_g = 1 Ω		40			
Fall Time	t _f			10			
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			37	Α	
Pulse Diode Forward Current ^a	I _{SM}				105	_ ^	
Body Diode Voltage	V_{SD}	I _S = - 3 A		- 0.5	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			93		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	L = 3 A dl/dt = 100 A/us T = 25 °C		65		nC	
Reverse Recovery Fall Time	t _a	$I_F = 3 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		76			
Reverse Recovery Rise Time	t _b			18		ns	

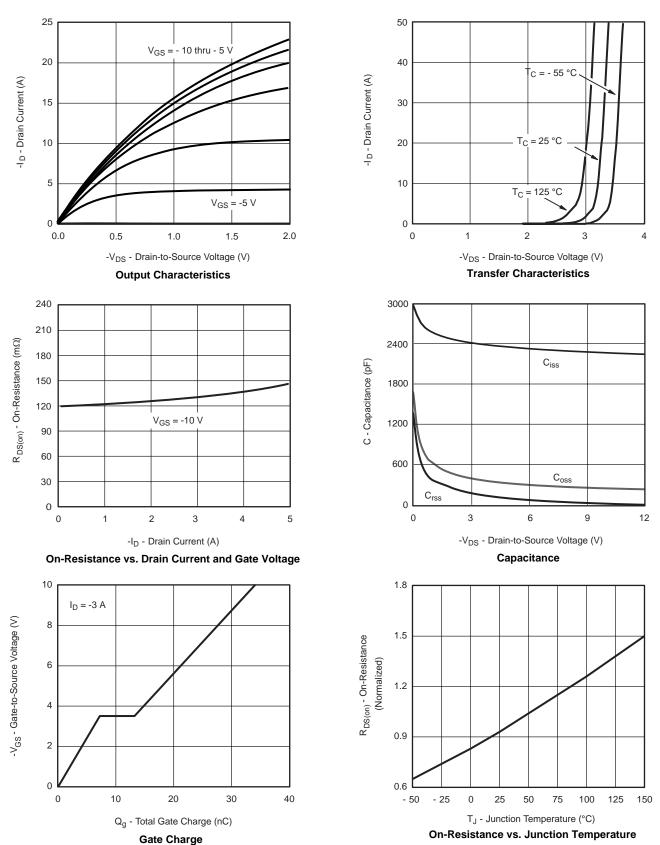
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

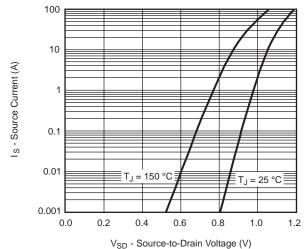
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



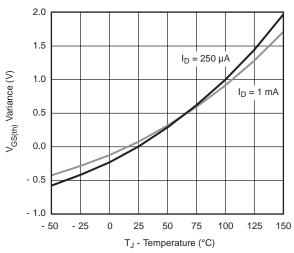




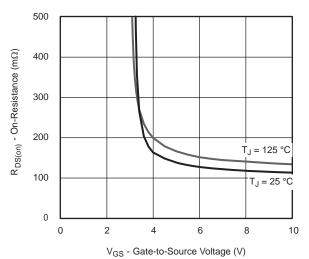


VSD - Source-to-Drain voltage (V)

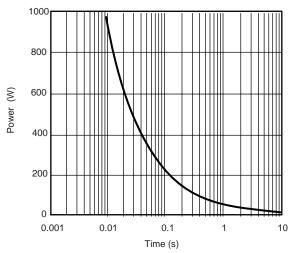
Source-Drain Diode Forward Voltage



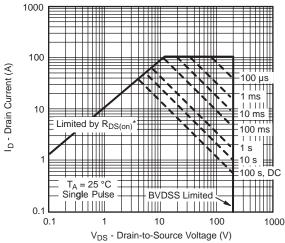
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



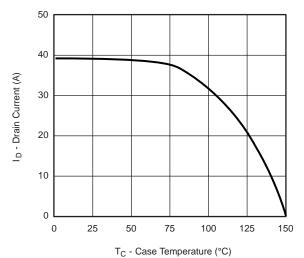
Single Pulse Power, Junction-to-Ambient



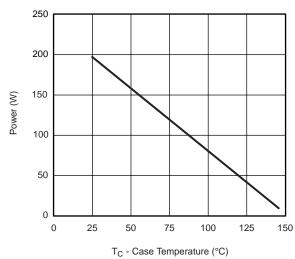
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

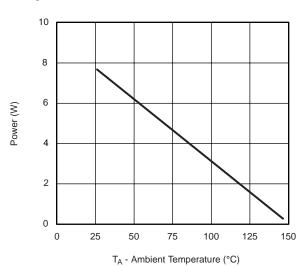
Safe Operating Area, Junction-to-Ambient





Current Derating*

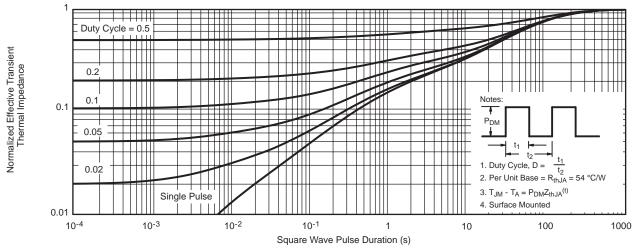




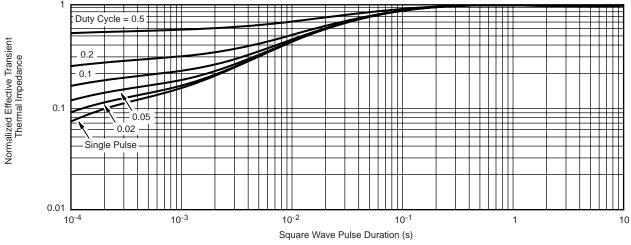
Power, Junction-to-Case Power, Junction-to-Ambient

 $^{^*}$ The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





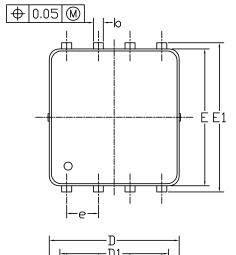
Normalized Thermal Transient Impedance, Junction-to-Ambient

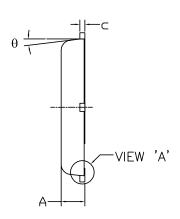


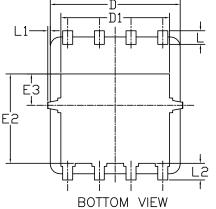
Normalized Thermal Transient Impedance, Junction-to-Case

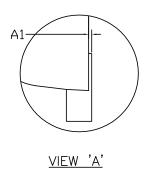
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DFN5x6_8L_EP1_P PACKAGE OUTLIN



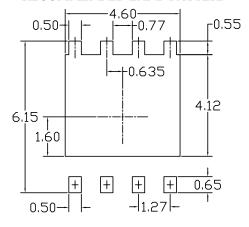






(SCALE 5:1)

RECOMMENDED LAND PATTERN



GVA (DOLG	DIMENS	SIONS IN MILLI	METERS	DIMENSIONS IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0. 95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
c	0.15	0. 20	0. 25	0.006	0.008	0.010	
D	4. 80	5. 20	5. 30	0. 201	0. 205	0. 209	
D1	4. 25	4. 35	4. 45	0. 167	0.171	0. 175	
Е	5. 45	5. 55	5. 65	0. 215	0. 219	0. 222	
E1	5. 95	6.05	6. 15	0. 234	0. 238	0. 242	
E2	3. 525	3. 625	3. 725	0. 139	0. 143	0. 147	
E3	1. 175	1. 275	1. 375	0.046	0.050	0.054	
e	1. 27 BSC			0.050 BSC			
L	0.45	0. 55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	

NOTE

- UNIT: mm
- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- 2. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.





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